

NJ903 Process

Silicon Junction Field-Effect Transistor

- Analog Switch
- Digital Switch
- Low-Noise Amplifier

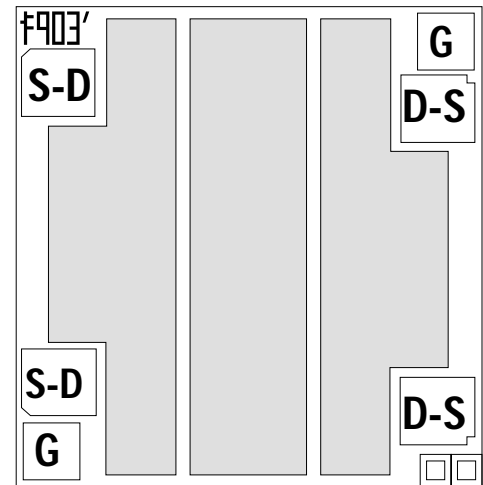
Absolute maximum ratings at TA = 25 °C

Gate Current, I _g	10 mA
Operating Junction Temperature, T _j	+150°C
Storage Temperature, T _s	- 65°C to +175°C

Devices in this Databook based on the NJ903 Process.

Datasheet

IFN5432
IFN5433
IFN5434



Die Size = 0.040" X 0.040"
All Bond Pads = 0.004" Sq.
Substrate is also Gate.

At 25°C free air temperature:

Static Electrical Characteristics

		NJ903 Process						
		Min	Typ	Max	Unit	Test Conditions		
Gate Source Breakdown Voltage	V _{(BR)GSS}	- 25	- 40		V	I _G = - 1 μA, V _{DS} = 0V		
Reverse Gate Leakage Current	I _{GSS}		- 0.1	- 1	nA	V _{GS} = - 15V, V _{DS} = 0V		
Drain Saturation Current (Pulsed)	I _{DSS}	100		900	mA	V _{DS} = 10V, V _{GS} = 0V		
Gate Source Cutoff Voltage	V _{GS(OFF)}	- 2		- 7	V	V _{DS} = 10V, I _D = 1 nA		

Dynamic Electrical Characteristics

Drain Source ON Resistance	r _{ds(on)}		5		Ω	I _D = 1 mA, V _{GS} = 0	f = 1 kHz
Input Capacitance	C _{iss}		45		pF	V _{DS} = 0V, V _{GS} = - 10V	f = 1 MHz
Feedback Capacitance	C _{iss}		22		pF	V _{DS} = 0V, V _{GS} = - 10V	f = 1 MHz
Turn On Delay Time	t _{d(on)}		7		ns	V _{DD} = 1.5V, I _{D(ON)} = 30 mA R _L = 50 Ω, V _{GS(ON)} = 0V V _{GS(OFF)} = - 7V	
Rise Time	t _r		1		ns		
Turn Off Delay Time	t _{d(off)}		12		ns		
Fall Time	t _f		2		ns		



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